

**SANYO**

No.3099

**2SC4493**

NPN Triple Diffused Planar Silicon Transistor

High-Voltage Amp,  
High-Voltage Switching Applications**Features**

- High breakdown voltage
- Small  $c_{ob}$
- High reliability (adoption of HVP process)
- Intended for high-density mounting (Suitable for sets whose height is restricted)

**Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$** 

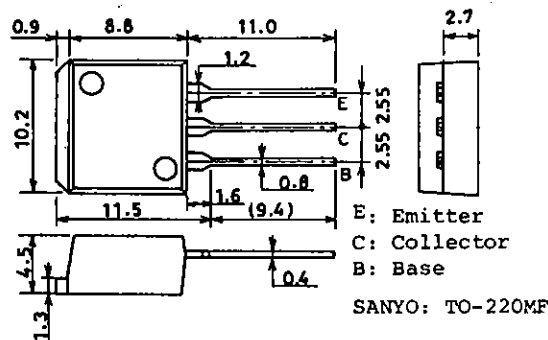
			unit
Collector to Base Voltage	$V_{CBO}$	800	V
Collector to Emitter Voltage	$V_{CEO}$	800	V
Emitter to Base Voltage	$V_{EBO}$	7	V
Collector Current	$I_C$	20	mA
Peak Collector Current	$i_{cp}$	60	mA
Collector Dissipation	$P_C$	1.65	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics at  $T_a = 25^\circ\text{C}$** 

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 800\text{V}, I_E = 0$			1	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$			1	$\mu\text{A}$
DC Current Gain	$h_{FE}(1)$	$V_{CE} = 5\text{V}, I_C = 2\text{mA}$	20		50	
	$h_{FE}(2)$	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$	10			
Gain-Bandwidth Product	$f_T$	$V_{CE} = 10\text{V}, I_C = 2\text{mA}$		40		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 2\text{mA}$			1	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{mA}, I_B = 2\text{mA}$			1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	800			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	800			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	7			V
Output Capacitance	$c_{ob}$	$V_{CB} = 100\text{V}, f = 1\text{MHz}$		1.6		pF

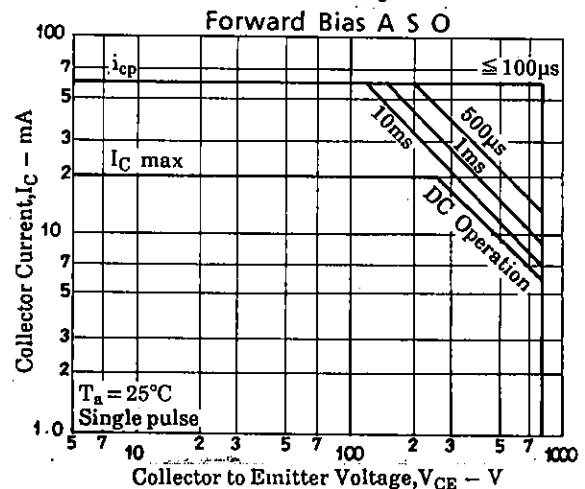
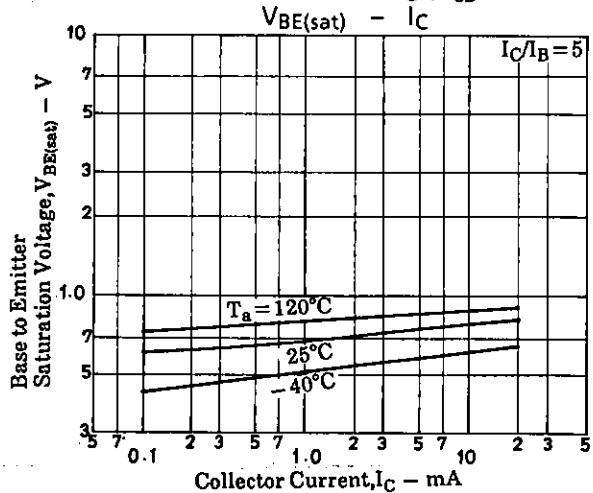
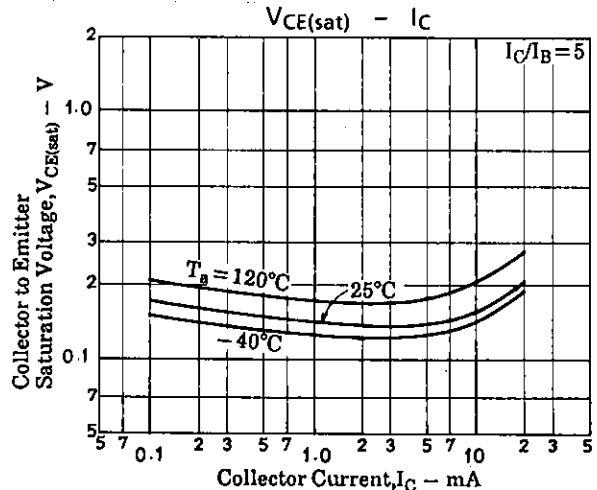
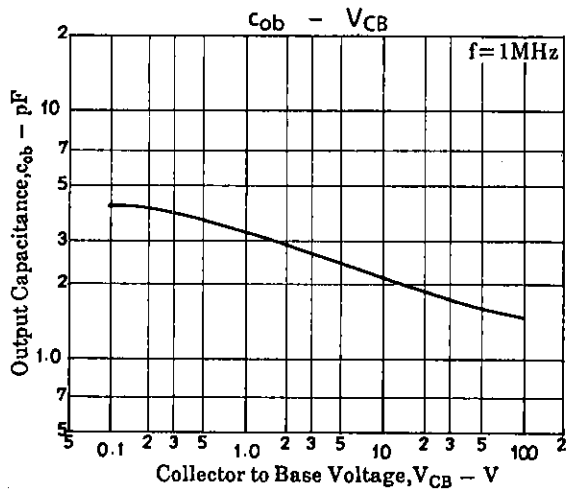
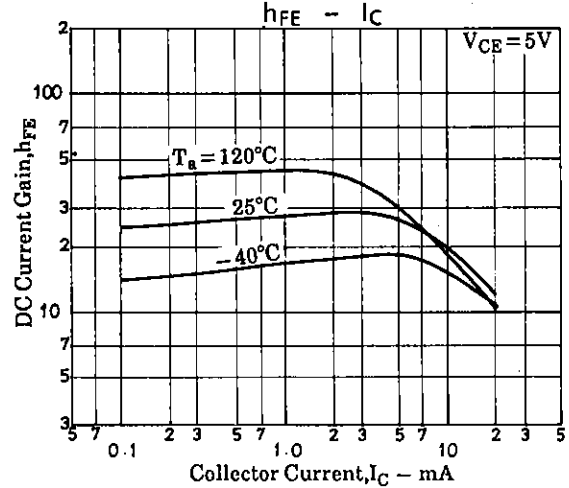
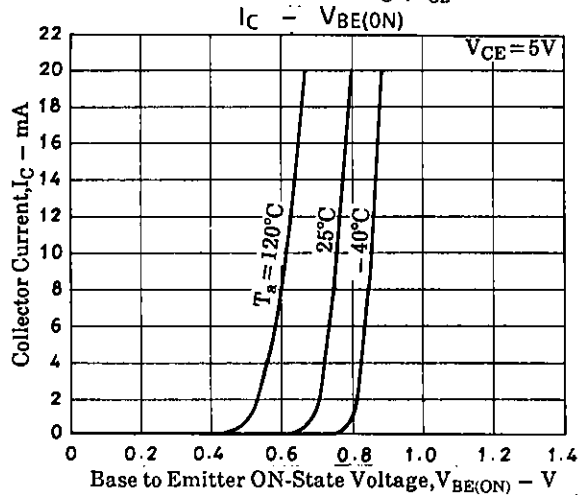
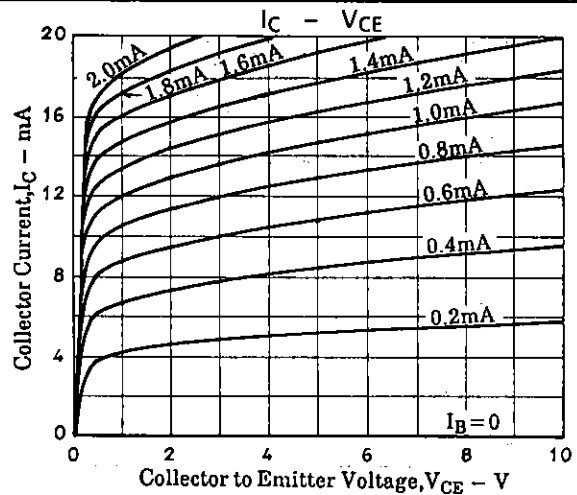
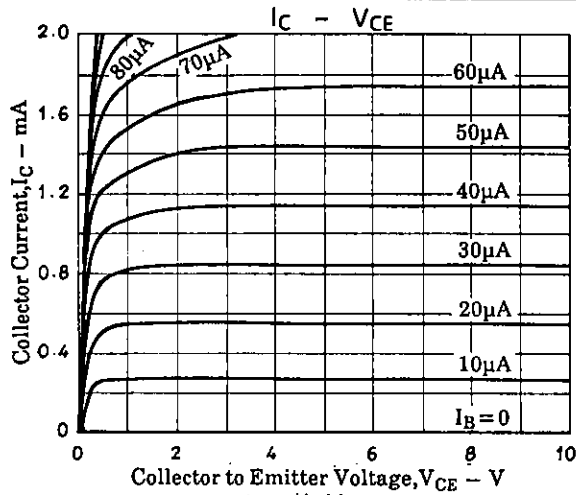
**Package Dimensions 2049B**

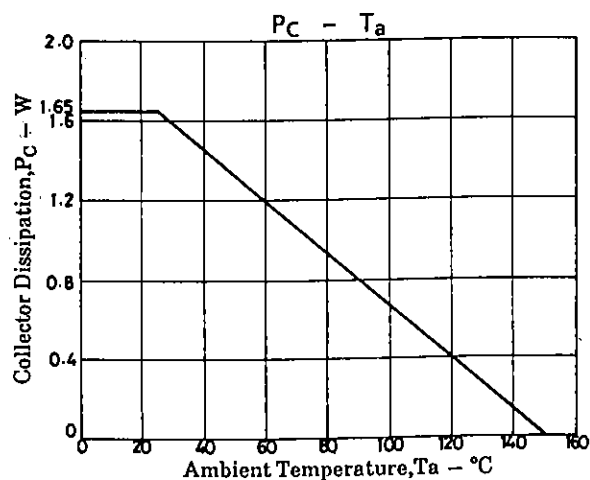
(unit: mm)

**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

4139MO, TS No.3099-1/3





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